

				J.		
Register Number						

Code: 15EC21T

II Semester Diploma Examination, Nov./Dec. 2018

BASICS OF SEMICONDUCTOR DEVICES

Time	e : 3 Hours] [Max. Marks : 10	0
Instr	uctions: (1) Answer any six questions from Part – A. $(6 \times 5 = 30 \text{ marks})$	
	(2) Answer any seven full questions from Part – B. $(7 \times 10 = 70 \text{ marks})$	
	PART – A	
1.	Sketch energy-band diagrams of insulator, semiconductor and conductor.	5
2.	Compare CE and CC modes of operation of BJT. FOXY ORO BY BETA CONSOLE	5
3.	Explain the relevance of heat sinks in BJT applications.	5
4.	Explain briefly the working of N-channel JFET.	5
5.	CMOS consumes very less power. Justify. Also, list disadvantages of CMOS family.	5
6.	Write the features of PIN diode.	5
7.	List the advantages and disadvantages of IC's.	5

16.	(a)	Write at least one application for each of the following:
		(i) Varactor
		(ii) SCR
		(iii) UJT
		(iv) Tunnel diode and
		(v) Triac
	(b)	Explain the principle of operation of SCR. 5
	(a)	Write note on Tunnel Diode. 5
	(b)	Outline the symbols of UJT, SCR, Varactor diode, Diac and PIN diode. 5
		FOXY ORO
18.	(a)	Explain the IC classification based on scale of integration. 5
	(b)	Describe the fabrication process of monolithic ICs. 5
19.	(a)	List the features of LASER. 5
	(b)	List the features of LED bulb.